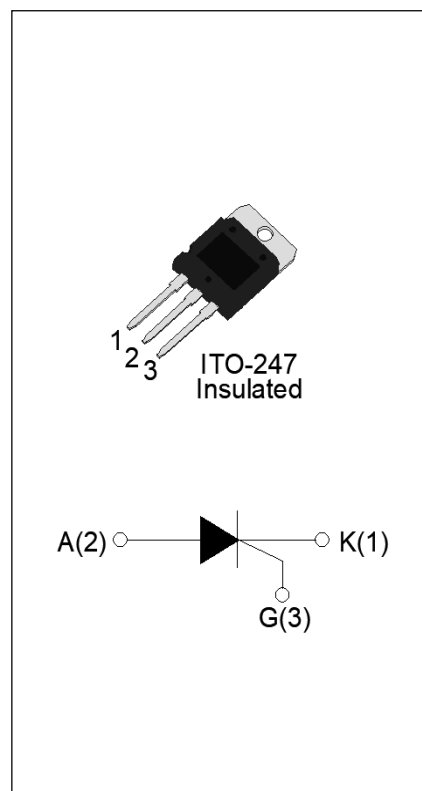




### DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT12110IS SCR provides high dv/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, UPS, SVC, power charger, T-tools etc. From all three terminals to external heatsink, JCT12110IS provides a rated insulation voltage of 2500 V<sub>RMS</sub>, Package ITO-247 is RoHS compliant.



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	110	A
$V_{DRM}/V_{RRM}$	1200	V
$I_{GT}$	10-80	mA

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	1200	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	1200	V
Average on-state current ( $T_c \leq 73^\circ\text{C}$ )	$I_{T(AV)}$	70	A
RMS on-state current ( $T_c \leq 73^\circ\text{C}$ )	$I_{T(RMS)}$	110	A
Non repetitive surge peak on-state current ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	1100	A
Non repetitive surge peak on-state current ( $t_p=8.3\text{ms}$ , $T_j=25^\circ\text{C}$ )		1200	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	6050	A <sup>2</sup> s
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	200	A/ $\mu\text{s}$

Peak gate current ( $t_p=20\mu s$ , $T_j=125^\circ C$ )	$I_{GM}$	12	A
Average gate power dissipation ( $T_j=125^\circ C$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	22	W
Peak pulse voltage ( $T_j=25^\circ C$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	1.3	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ C$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_L=33\Omega$	10	-	80	mA
$V_{GT}$		-	-	1.3	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3K\Omega$	0.25	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	250	mA
$I_H$	$I_T=1A$	-	-	200	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125^\circ C$	3000	-	-	V/ $\mu s$
$t_{on}$	$I_G=100mA$ $I_A=1A$ $I_R=100mA$ $T_j=25^\circ C$	-	8	-	$\mu s$
$t_{off}$		-	200	-	

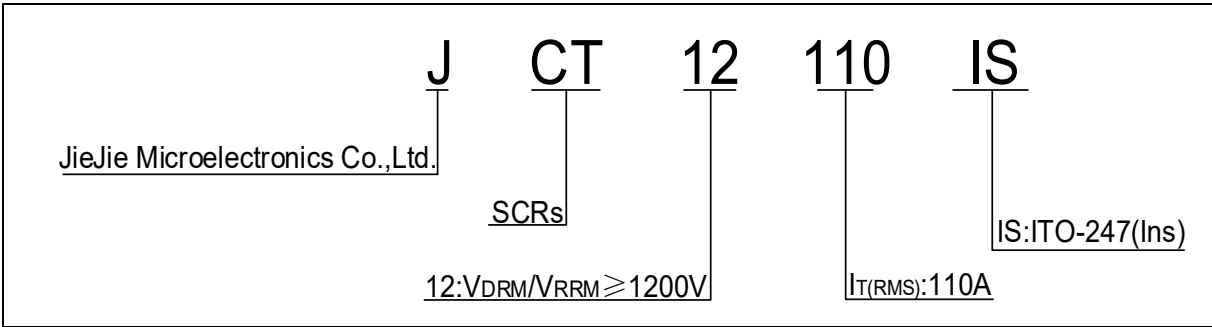
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=150A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.6	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ C$	0.76	V
$R_D$	Dynamic resistance	$T_j=125^\circ C$	5.6	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	10	$\mu A$
$I_{RRM}$		$T_j=125^\circ C$	8	mA

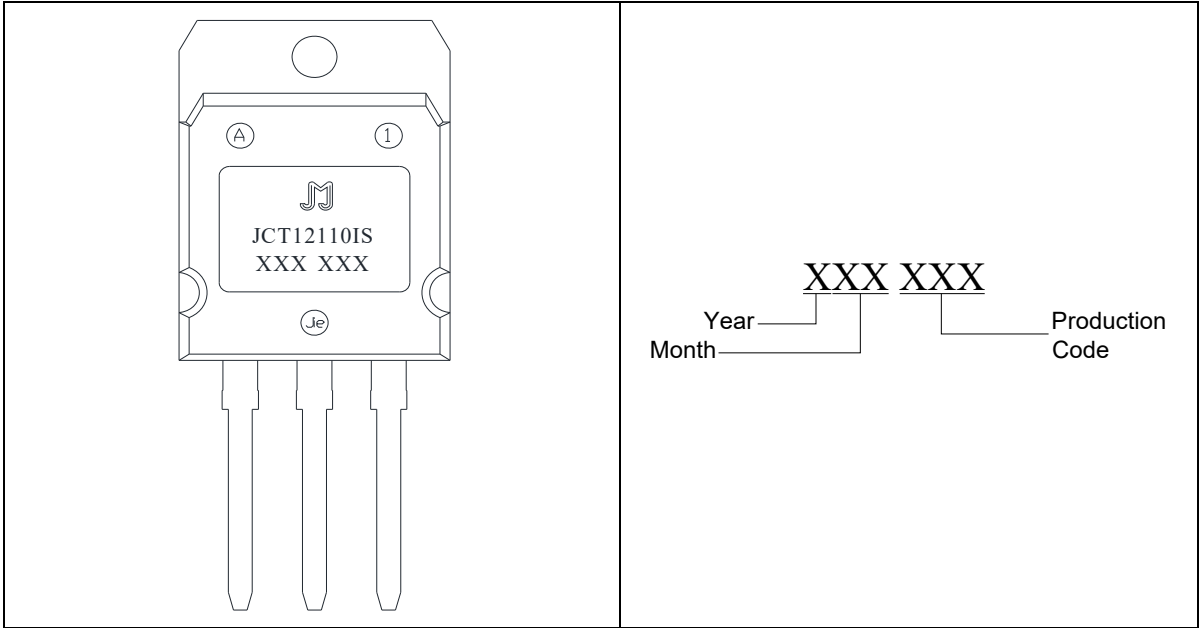
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.35	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	50	$^\circ C/W$

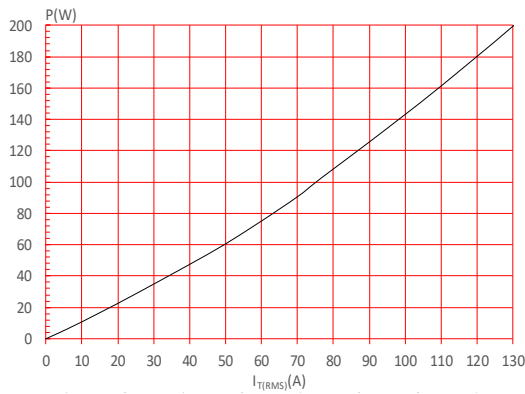
ORDERING INFORMATION



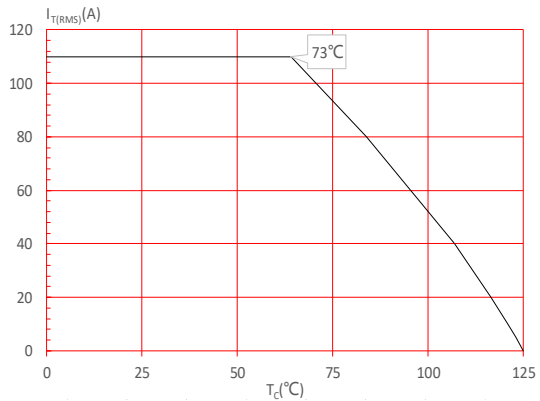
MARKING



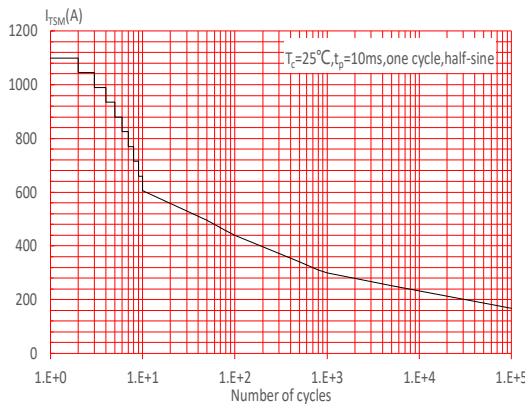
**FIG.1** Maximum power dissipation versus RMS on-state current



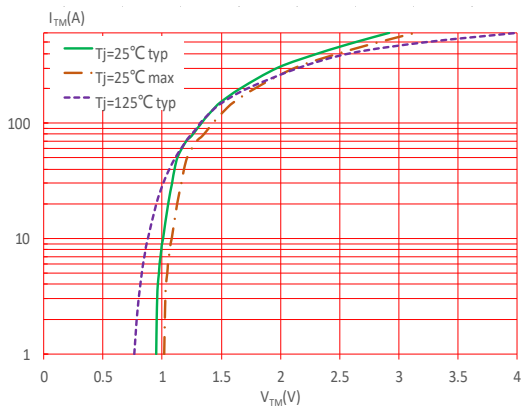
**FIG.2:** RMS on-state current versus case temperature



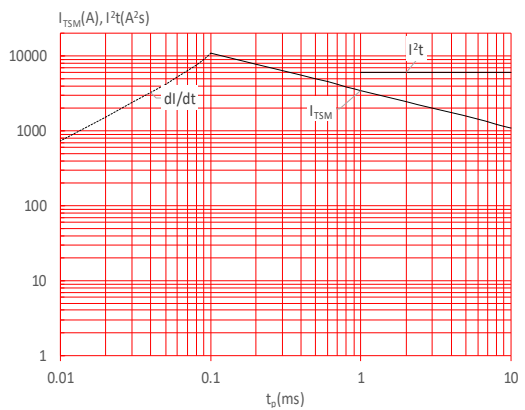
**FIG.3:** Surge peak on-state current versus number of cycles



**FIG.4:** On-state characteristics



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 200\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

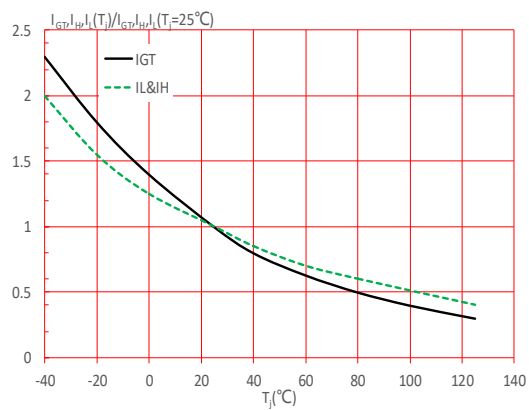
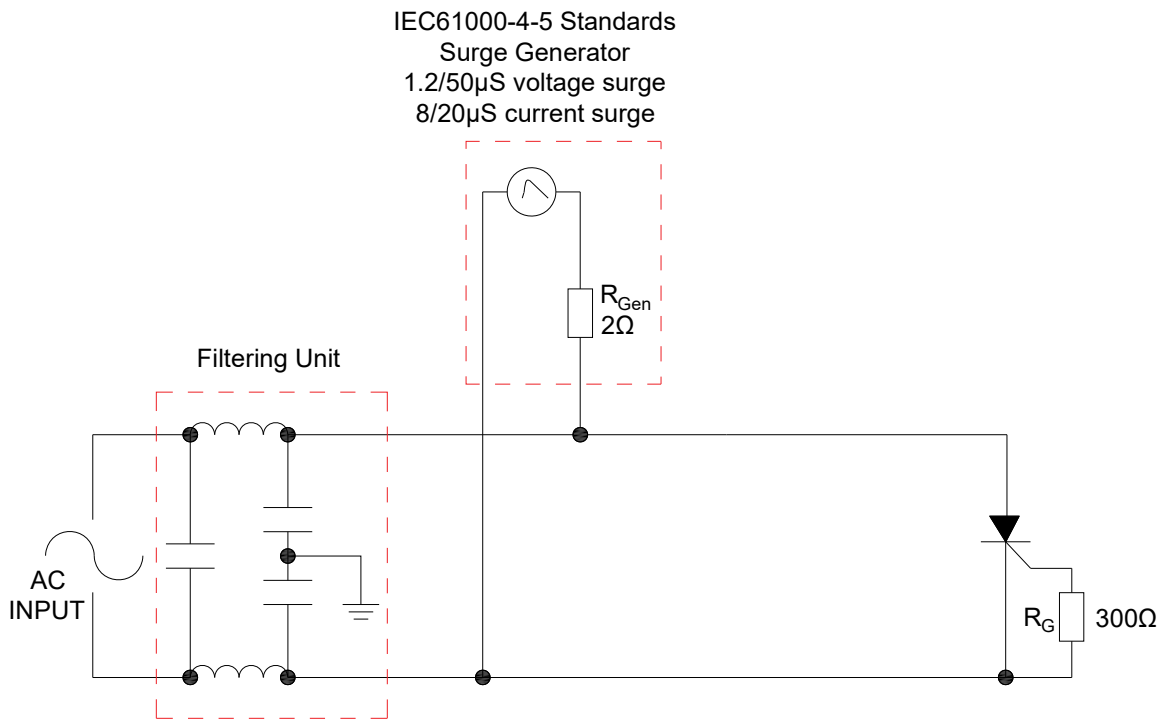


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

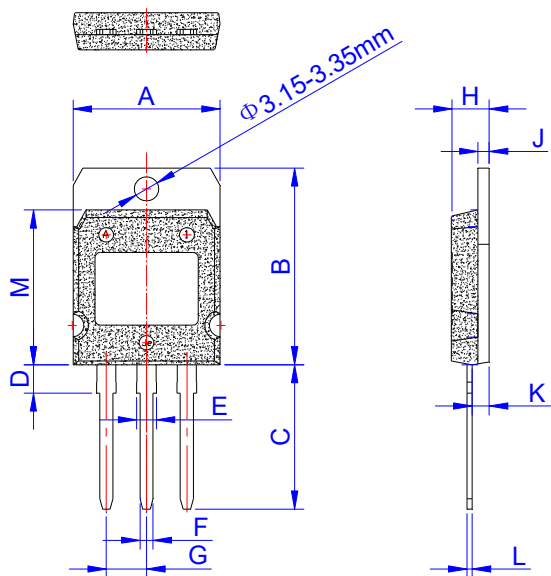
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT12110IS	1200	10-80	ITO-247(Ins)	25	Tube

**Document Revision History**

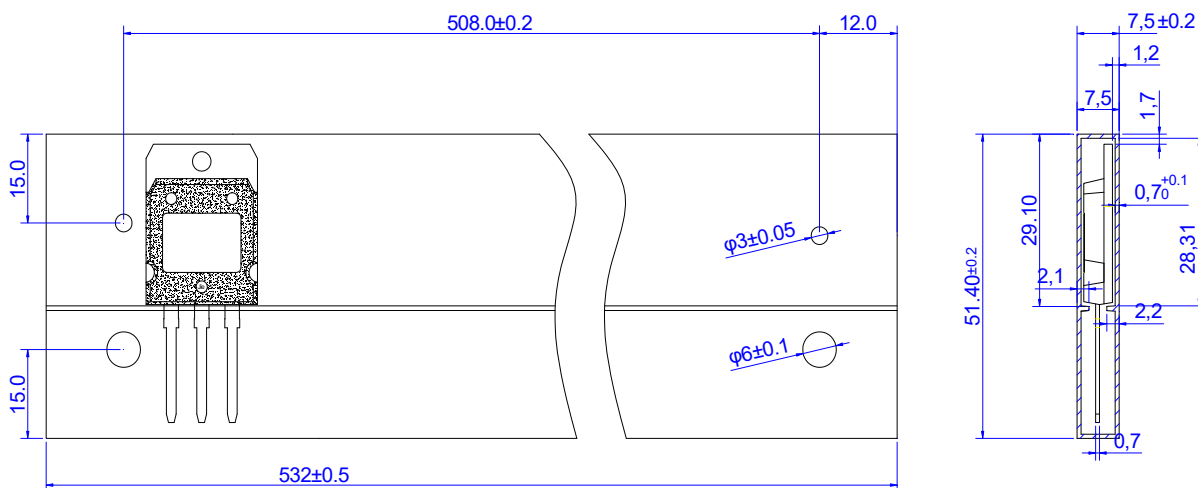
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.7	19.9	20.1	0.776	0.783	0.791
B	26.9	27.1	27.3	1.059	1.067	1.075
C	19.4	19.9	20.4	0.764	0.783	0.803
D	3.80	3.90	4.00	0.150	0.154	0.157
E	2.56	2.66	2.76	0.101	0.105	0.109
F	1.66	1.76	1.86	0.065	0.069	0.073
G	5.25		5.65	0.207		0.222
H	5.05	5.10	5.50	0.199	0.201	0.217
J	1.45	1.50	1.55	0.057	0.059	0.061
K	2.20	2.30	2.40	0.087	0.091	0.094
L	0.60	0.70	0.80	0.024	0.028	0.031
M	21.2	21.3	21.4	0.835	0.839	0.843

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600

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